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Team Nexperia



BCV63; BCV63B

NPN general-purpose double transistors Rev. 4 — 4 August 2010

Product data sheet

Product profile

1.1 General description

NPN general-purpose double transistors in a small SOT143B Surface-Mounted Device (SMD) plastic package.

Table 1. **Product overview**

| Type number | Package | | PNP complement |
|-------------|---------|-------|----------------|
| | NXP | JEITA | |
| BCV63 | SOT143B | - | - |
| BCV63B | | | BCV64B |

1.2 Features and benefits

- Low current (max. 100 mA)
- Low voltage (max. 30 V and 6 V)
- AEC-Q101 qualified
- Small SMD plastic package

1.3 Applications

- General-purpose switching and amplification
- For use in Schmitt trigger applications

1.4 Quick reference data

Table 2. **Quick reference data**

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------|---------------------------|--|-----|-----|-----|------|
| Per trans | istor | | | | | |
| I _C | collector current | | - | - | 100 | mA |
| Transistor TR1 | | | | | | |
| V_{CEO} | collector-emitter voltage | open base | - | - | 30 | V |
| h _{FE} | DC current gain | $V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}$ | | | | |
| | BCV63 | | 110 | - | 800 | |
| | BCV63B | | 200 | - | 450 | |



Table 2. Quick reference data ...continued

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|-----------------|---------------------------|---|-----|-----|-----|------|
| Transisto | r TR2 | | | | | |
| V_{CEO} | collector-emitter voltage | open base | - | - | 6 | V |
| h _{FE} | DC current gain | $V_{CE} = 700 \text{ mV}; I_{C} = 2 \text{ mA}$ | [1] | | | |
| | BCV63 | | 110 | - | 800 | |
| | BCV63B | | 200 | - | 450 | |

^[1] Group selection will be done on TR1. Due to matched dies, h_{FE} values for TR2 are the same as for TR1.

Pinning information 2.

| Table 3. | Pinning | | |
|----------|----------------------------|--------------------|----------------|
| Pin | Description | Simplified outline | Graphic symbol |
| 1 | collector TR2 and base TR1 | | 2 4 |
| 2 | collector TR1 | 4 3 | |
| 3 | emitter TR1 and TR2 | | TR1 |
| 4 | base TR2 | 1 2 | TR2 |

Ordering information

Table 4. **Ordering information**

| Type number | Package | | |
|-------------|---------|--|---------|
| | Name | Description | Version |
| BCV63 | - | plastic surface-mounted package; 4 leads | SOT143B |
| BCV63B | | | |

Marking 4.

Table 5. **Marking codes**

| Type number | Marking code ^[1] |
|-------------|-----------------------------|
| BCV63 | *D5 |
| BCV63B | *D6 |

- [1] * = -: made in Hong Kong
 - * = p: made in Hong Kong
 - * = t: made in Malaysia
 - * = W: made in China

006aab228

5. Limiting values

Table 6. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

| Symbol | Parameter | Conditions | Min | Max | Unit |
|------------------|---------------------------|-----------------------------|--------------|------|------|
| Per trans | istor | | | | |
| V_{EBO} | emitter-base voltage | open collector | - | 6 | V |
| I _C | collector current | | - | 100 | mA |
| I _{CM} | peak collector current | | - | 200 | mA |
| I _B | base current | | - | 100 | mA |
| Transisto | or TR1 | | | | |
| V_{CBO} | collector-base voltage | open emitter | - | 30 | V |
| V_{CEO} | collector-emitter voltage | open base | - | 30 | V |
| Transisto | or TR2 | | | | |
| V_{CBO} | collector-base voltage | open emitter | - | 6 | V |
| V_{CEO} | collector-emitter voltage | open base | - | 6 | V |
| Per device | ce | | | | |
| P _{tot} | total power dissipation | $T_{amb} \leq 25 ^{\circ}C$ | <u>[1]</u> _ | 250 | mW |
| Tj | junction temperature | | - | 150 | °C |
| T _{amb} | ambient temperature | | -65 | +150 | °C |
| T _{stg} | storage temperature | | -65 | +150 | °C |
| | | | | | |

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB).

6. Thermal characteristics

Table 7. Thermal characteristics

| Symbol | Parameter | Conditions | Min | Тур | Max | Unit |
|---------------|---|-------------|--------------|-----|-----|------|
| $R_{th(j-a)}$ | thermal resistance from junction to ambient | in free air | <u>[1]</u> - | - | 500 | K/W |

^[1] Device mounted on an FR4 PCB.

7. Characteristics

Table 8. Characteristics

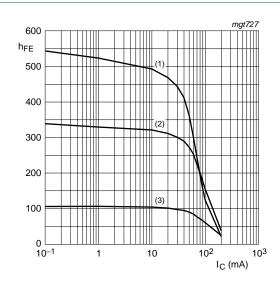
 $T_i = 25$ °C unless otherwise specified

| Symbol | Parameter | Conditions | | Min | Тур | Max | Unit |
|--------------------|--------------------------------------|---|-----|-----|-----|-----|------|
| Per tran | sistor | | | | | | |
| I _{CBO} | collector-base | $V_{CB} = 30 \text{ V}; I_E = 0 \text{ A}$ | | - | - | 15 | nA |
| | cut-off current | $V_{CB} = 30 \text{ V}; I_E = 0 \text{ A};$ $T_j = 150 \text{ °C}$ | | - | - | 5 | μА |
| V _{CEsat} | collector-emitter saturation voltage | $I_C = 10 \text{ mA};$ $I_B = 0.5 \text{ mA}$ | | - | 75 | 300 | mV |
| V _{BEsat} | base-emitter saturation voltage | $I_C = 10 \text{ mA};$ $I_B = 0.5 \text{ mA}$ | [2] | - | 700 | - | mV |
| Transis | or TR1 | | | | | | |
| h _{FE} | DC current gain | $V_{CE} = 5 \text{ V}; I_{C} = 2 \text{ mA}$ | | | | | |
| | BCV63 | | | 110 | - | 800 | |
| | BCV63B | | | 200 | - | 450 | |
| V _{CEsat} | collector-emitter saturation voltage | $I_C = 100 \text{ mA}; I_B = 5 \text{ mA}$ | | - | 250 | 650 | mV |
| V _{BEsat} | base-emitter saturation voltage | $I_C = 100 \text{ mA}; I_B = 5 \text{ mA}$ | [2] | - | 850 | - | mV |
| V_{BE} | base-emitter voltage | $I_C = 2 \text{ mA}; V_{CE} = 5 \text{ V}$ | [3] | 600 | 650 | 750 | mV |
| | | $I_C = 10 \text{ mA}; V_{CE} = 5 \text{ V}$ | [3] | - | - | 820 | mV |
| f _T | transition frequency | $V_{CE} = 5 \text{ V}; I_{C} = 10 \text{ mA};$ f = 100 MHz | | 100 | - | - | MHz |
| C _c | collector capacitance | $V_{CB} = 10 \text{ V};$ $I_E = i_e = 0 \text{ A}; f = 1 \text{ MHz}$ | | - | 4 | - | pF |
| Transis | or TR2 | | | | | | |
| h _{FE} | DC current gain | $V_{CE} = 700 \text{ mV};$ $I_C = 2 \text{ mA}$ | [1] | | | | |
| | BCV63 | | | 110 | - | 800 | |
| | BCV63B | | | 200 | - | 450 | |
| V _{CEsat} | collector-emitter saturation voltage | $I_C = 100 \text{ mA}; I_B = 5 \text{ mA}$ | | - | 250 | - | mV |
| V_{BE} | base-emitter voltage | $I_C = 2 \text{ mA};$ $V_{CE} = 700 \text{ mV}$ | [3] | - | 700 | - | mV |

^[1] Group selection will be done on TR1. Due to matched dies, h_{FE} values for TR2 are the same as for TR1.

^[2] V_{BEsat} decreases by about 1.7 mV/K with increasing temperature.

^[3] V_{BE} decreases by about 2 mV/K with increasing temperature.



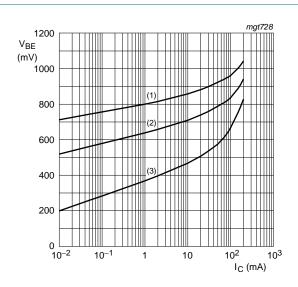
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = -55 \, ^{\circ}C$

Fig 1. BCV63B: DC current gain as a function of collector current; typical values



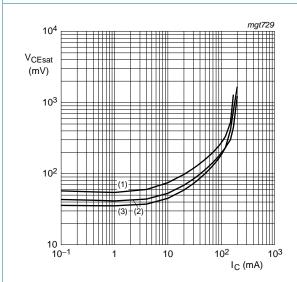
$$V_{CE} = 5 V$$

(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig 2. BCV63B: Base-emitter voltage as a function of collector current; typical values



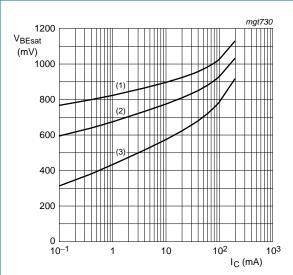


(1)
$$T_{amb} = 150 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3)
$$T_{amb} = -55 \, ^{\circ}C$$

Fig 3. BCV63B: Collector-emitter saturation voltage as a function of collector current; typical values



$$I_{\rm C}/I_{\rm B} = 10$$

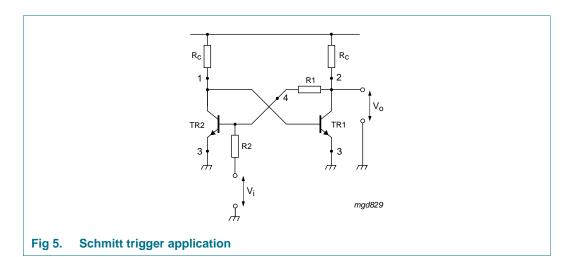
(1)
$$T_{amb} = -55 \, ^{\circ}C$$

(2)
$$T_{amb} = 25 \, ^{\circ}C$$

(3) $T_{amb} = 150 \, ^{\circ}C$

Fig 4. BCV63B: Base-emitter saturation voltage as a function of collector current; typical values

8. Application information

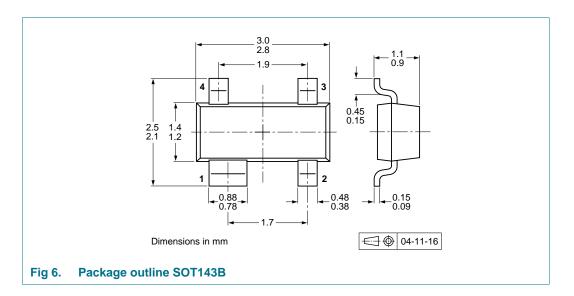


9. Test information

9.1 Quality information

This product has been qualified in accordance with the Automotive Electronics Council (AEC) standard *Q101 - Stress test qualification for discrete semiconductors*, and is suitable for use in automotive applications.

10. Package outline



11. Packing information

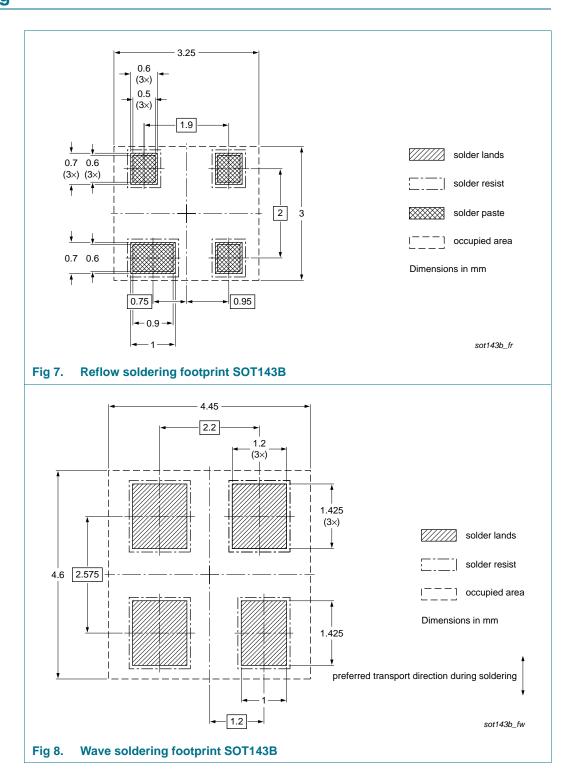
Table 9. Packing methods

The indicated -xxx are the last three digits of the 12NC ordering code.[1]

| Type number | Package | Description | Packing quantity | |
|-------------|---------|--------------------------------|------------------|-------|
| | | | 3000 | 10000 |
| BCV63 | SOT143B | 4 mm pitch, 8 mm tape and reel | -215 | -235 |
| BCV63B | | | | |

^[1] For further information and the availability of packing methods, see <u>Section 14</u>.

12. Soldering



13. Revision history

Table 10. Revision history

| Document ID | Release date | Data sheet status | Change notice | Supersedes | |
|----------------|---|--|------------------------|-----------------------|--|
| | | | Change notice | • | |
| BCV63_63B v.4 | 20100804 | Product data sheet | - | BCV63_BCV63B_3 | |
| Modifications: | | of this data sheet has been of NXP Semiconductors. | redesigned to comply w | vith the new identity | |
| | Legal texts | have been adapted to the ne | ew company name whe | ere appropriate. | |
| | Section 1 "F | Product profile": amended | | | |
| | Section 3 "Ordering information": added | | | | |
| | Section 4 "Marking": updated | | | | |
| | • Figure 1, 2, 3 and 4: added | | | | |
| | Section 8 "A | Application information": add | ed | | |
| | Section 9 "" | est information": added | | | |
| | • Figure 6: su | perseded by minimized pac | kage outline drawing | | |
| | Section 11 ' | "Packing information": added | d | | |
| | Section 12 "Soldering": added | | | | |
| | Section 14 | 'Legal information": updated | | | |
| BCV63_BCV63B_3 | 19990521 | Product specification | - | BCV63_CNV_2 | |
| BCV63_CNV_2 | 19970310 | Product specification | - | - | |
| | | | | | |

14. Legal information

14.1 Data sheet status

| Document status[1][2] | Product status[3] | Definition |
|--------------------------------|-------------------|---|
| Objective [short] data sheet | Development | This document contains data from the objective specification for product development. |
| Preliminary [short] data sheet | Qualification | This document contains data from the preliminary specification. |
| Product [short] data sheet | Production | This document contains the product specification. |

- [1] Please consult the most recently issued document before initiating or completing a design.
- [2] The term 'short data sheet' is explained in section "Definitions"
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BCV63_63B

BCV63; BCV63B

NPN general-purpose double transistors

Quick reference data — The Quick reference data is an extract of the product data given in the Limiting values and Characteristics sections of this document, and as such is not complete, exhaustive or legally binding.

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